

## **NCE N-Channel Super Trench II Power MOSFET**

#### **Description**

The series of devices uses **Super Trench II** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of  $R_{\text{DS(ON)}}$  and  $Q_g$ . This device is ideal for high-frequency switching and synchronous rectification.

### **Application**

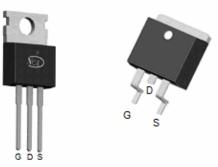
- DC/DC Converter
- •Ideal for high-frequency switching and synchronous rectification

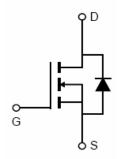
#### **General Features**

- $V_{DS}$  =85V, $I_D$  =120A  $R_{DS(ON)}$ =4.45m $\Omega$  , typical (TO-220)@  $V_{GS}$ =10V  $R_{DS(ON)}$ =4.25m $\Omega$  , typical (TO-263)@  $V_{GS}$ =10V
- Excellent gate charge x R<sub>DS(on)</sub> product(FOM)
- Very low on-resistance R<sub>DS(on)</sub>
- 175 °C operating temperature
- Pb-free lead plating

100% UIS TESTED! 100% ΔVds TESTED!

TO-220 TO-263





**Schematic Diagram** 

#### Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
NCEP048N85	NCEP048N85	TO-220	-	-	-
NCEP048N85D	NCEP048N85D	TO-263	-	-	-

### Absolute Maximum Ratings (T<sub>C</sub>=25 ℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V <sub>DS</sub>	85	V
Gate-Source Voltage	V <sub>G</sub> s	±20	V
Drain Current-Continuous	I <sub>D</sub>	120	А
Drain Current-Continuous(T <sub>C</sub> =100 °C)	I <sub>D</sub> (100℃)	92	А
Pulsed Drain Current	I <sub>DM</sub>	480	Α
Maximum Power Dissipation	P <sub>D</sub>	150	W
Derating factor		1.0	W/°C
Single pulse avalanche energy (Note 5)	E <sub>AS</sub>	660	mJ
Operating Junction and Storage Temperature Range	$T_{J}, T_{STG}$	-55 To 175	$^{\circ}$ C



# NCEP048N85, NCEP048N85D

V1.0

### **Thermal Characteristic**

Thermal Resistance, Junction-to-Case <sup>(Note 2)</sup>	R <sub>eJC</sub>	1.0	°C/W	
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Electrical Characteristics (T<sub>C</sub>=25°C unless otherwise noted)

Parameter	Symbol	Condition		Min	Тур	Max	Unit
Off Characteristics				•			
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =250μA		85		-	V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =85V,V <sub>GS</sub> =0V		-	-	1	μA
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±20V,V <sub>D</sub>	os=0V	-	-	±100	nA
On Characteristics (Note 3)					<u>I</u>		l
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS},I_{D}=2$	50μΑ	2.0	3.0	4.0	V
Danier Courses Our Otata Basistana	Б	V <sub>GS</sub> =10V, I <sub>D</sub> =60A	TO-220	-	4.45	4.8	mΩ
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>		TO-263		4.25	4.8	mΩ
Forward Transconductance	<b>g</b> fs	V <sub>DS</sub> =5V,I <sub>D</sub> =60A			65	-	S
Dynamic Characteristics (Note4)				•			
Input Capacitance	C <sub>lss</sub>	V <sub>DS</sub> =40V,V <sub>GS</sub> =0V, F=1.0MHz		-	3780	-	PF
Output Capacitance	Coss			-	740	-	PF
Reverse Transfer Capacitance	C <sub>rss</sub>			-	30	-	PF
Switching Characteristics (Note 4)				•			
Turn-on Delay Time	t <sub>d(on)</sub>			-	21	-	nS
Turn-on Rise Time	t <sub>r</sub>	$V_{DD}$ =40V, $I_{D}$ =60A $V_{GS}$ =10V, $R_{G}$ =1.6 $\Omega$		-	61	-	nS
Turn-Off Delay Time	t <sub>d(off)</sub>			-	40	-	nS
Turn-Off Fall Time	t <sub>f</sub>			-	12	-	nS
Total Gate Charge	Qg	\/ 40\/ I	004	-	71	-	nC
Gate-Source Charge	Q <sub>gs</sub>	V <sub>DS</sub> =40V,I <sub>D</sub> =60A, V <sub>GS</sub> =10V		-	21		nC
Gate-Drain Charge	$Q_{gd}$			-	22		nC
Drain-Source Diode Characteristics				•			
Diode Forward Voltage (Note 3)	$V_{SD}$	V <sub>GS</sub> =0V,I <sub>S</sub> =60A		-		1.2	V
Diode Forward Current (Note 2)	Is			-	-	120	Α
Reverse Recovery Time	t <sub>rr</sub>	$T_J = 25^{\circ}C, I_F = I_S$		-	67	-	nS
Reverse Recovery Charge	Qrr	$di/dt = 100A/\mu s^{(Note3)}$		-	137	-	nC

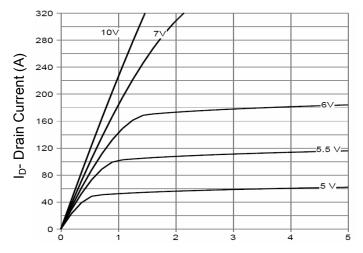
#### Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2. Surface Mounted on FR4 Board, t ≤ 10 sec.
- 3. Pulse Test: Pulse Width  $\leq$  300 $\mu$ s, Duty Cycle  $\leq$  2%.
- 4. Guaranteed by design, not subject to production
- 5. EAS condition : Tj=25  $^{\circ}\text{C}$  ,V\_DD=40V,V\_G=10V,L=0.5mH,Rg=25 $\Omega$

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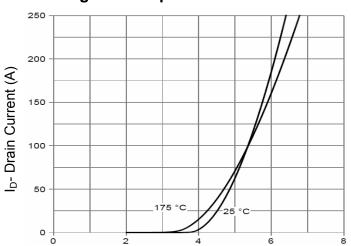


### **Typical Electrical and Thermal Characteristics**



Vds Drain-Source Voltage (V)

**Figure 1 Output Characteristics** 



Vgs Gate-Source Voltage (V)

**Figure 2 Transfer Characteristics** 

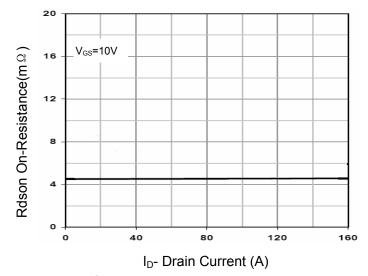
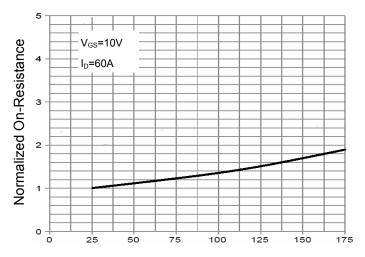
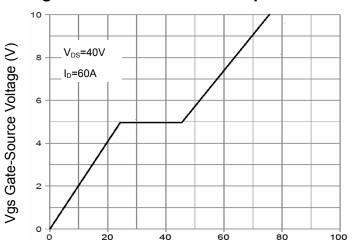


Figure 3 Rdson- Drain Current

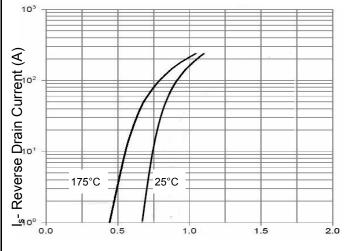


T<sub>J</sub>-Junction Temperature(°C)

**Figure 4 Rdson-Junction Temperature** 



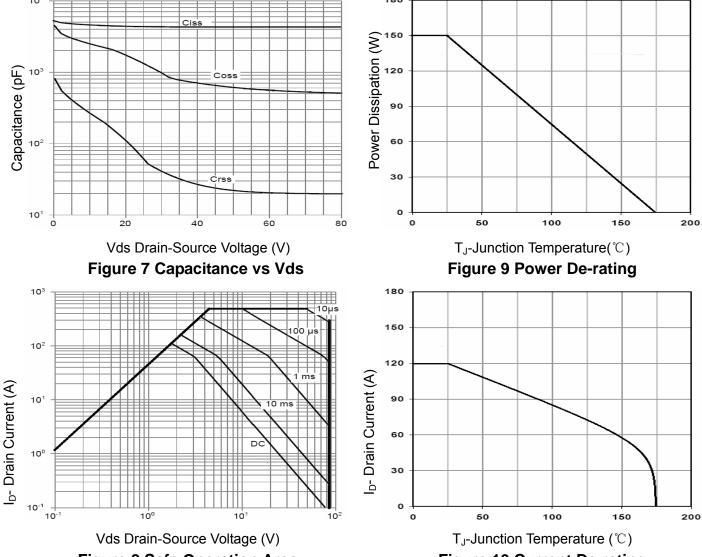
Qg Gate Charge (nC)
Figure 5 Gate Charge



Vsd Source-Drain Voltage (V)

Figure 6 Source- Drain Diode Forward

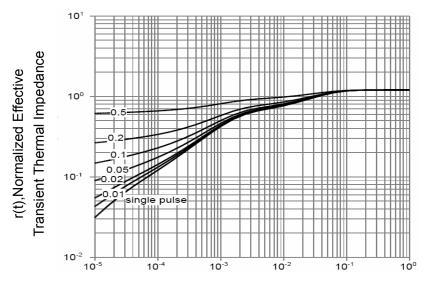




**Figure 8 Safe Operation Area** 

Figure 10 Current De-rating

V1.0



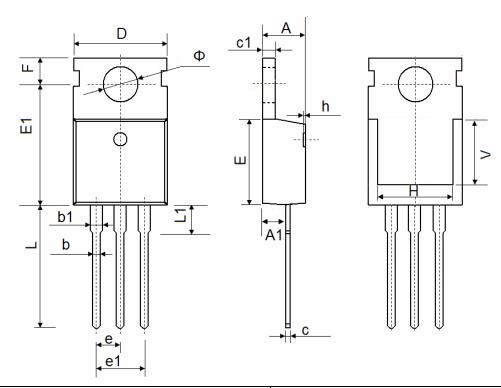
Square Wave Pluse Duration(sec)

Figure 11 Normalized Maximum Transient Thermal Impedance

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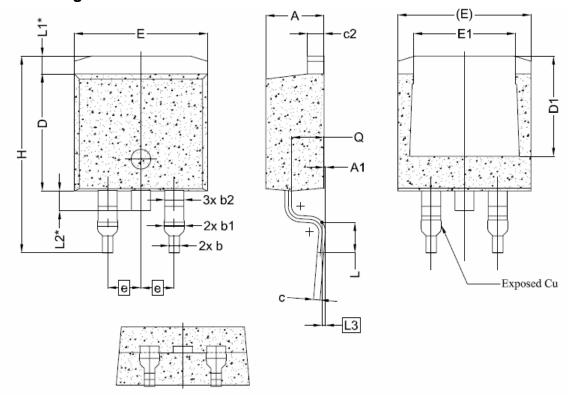
## **TO-220-3L Package Information**



Cumbal	Dimensions	In Millimeters	Dimensions In Inches		
Symbol	Min.	Max.	Min.	Max.	
А	4.400	4.600	0.173	0.181	
A1	2.250	2.550	0.089	0.100	
b	0.710	0.910	0.028	0.036	
b1	1.170	1.370	0.046	0.054	
С	0.330	0.650	0.013	0.026	
c1	1.200	1.400	0.047	0.055	
D	9.910	10.250	0.390	0.404	
Е	8.9500	9.750	0.352	0.384	
E1	12.650	12.950	0.498	0.510	
е	2.540 TYP.		0.100 TYP.		
e1	4.980	5.180	0.196	0.204	
F	2.650	2.950	0.104	0.116	
Н	7.900	8.100	0.311	0.319	
h	0.000	0.300	0.000	0.012	
L	12.900	13.400	0.508	0.528	
L1	2.850	3.250	0.112	0.128	
V	6.900	.900 REF. 0.276 REF.		REF.	
Ф	3.400	3.800	0.134	0.150	



## **TO-263-2L Package Information**



Completed.	Dimensions In Millimeters					
Symbol	Min.	Nom.	Max.			
A	4.24	4.44	4.64			
A1	0.00	0.10	0.25			
b	0.70	0.80	0.90			
b1	1.20	1.55	1.75			
b2	1.20	1.45	1.70			
С	0.40	0.50	0.60			
c2	1.15	1.27	1.40			
D	8.82	8.92	9.02			
D1	6.86	7.65	-			
E	9.96	10.16	10.36			
E1	6.89	7.77	7.89			
е	2.54BSC					
Н	14.61	14.61 15.00				
L	1.78 2.32		2.79			
L1	1.36 REF.					
L2	1.50 REF.					
L3	0.25 BSC					
Q	2.30	2.48	2.70			



## NCEP048N85, NCEP048N85D

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